

ABSTRACT OF THE DISCLOSURE

The cleaning of silicon carbide materials on a large-scale is described. Certain silicon carbide materials in the form of wafer-lift pins, wafer-rings and/or wafer-showerheads are cleaned by using a combination of two or more of the following 5 steps, comprising: high temperature oxidation, scrubbing, ultrasonic assisted etching in an aqueous acid solution, ultrasonication in deionized water, immersion in an aqueous acid solution, and high temperature baking. The silicon carbide materials may either be sintered or formed by chemical vapor deposition.